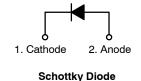
# Onsemi

## Silicon Carbide (SiC) **Schottky Diode** – EliteSiC, 15 A, 1200 V, D1, TO-247-2L



## **FFSH15120A**

#### Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

#### Features

- Max Junction Temperature 175°C
- Avalanche Rated 145 mJ

TO-247-2LD CASE 340CL MARKING DIAGRAM An and eling
An and eling
No Reverse Recovery/No Forward Recovery
This Device is Pb–Free, Halogen Free/BFR Free and RoHS Compliant
Applications
General Purpose
SMPS, Solar Inverter, UPS
Power Switching Circuits
A YWW ZZ FFSH15120A AYWWZZ FFSH 15120A = Assembly Plant Code = Date Code (Year & Week) = Lot Code = Specific Device Code

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

Symbol	Parameter	Value	Unit	
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage	1200	V	
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)	145	mJ	
١ <sub>F</sub>	Continuous Rectified Forward Current @ $T_C < T_C$	15	А	
	Continuous Rectified Forward Current @ $T_C$ <	26	А	
I <sub>F,Max</sub>	Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25°C, 10 μs	920	А
		T <sub>C</sub> = 150°C, 10 μs	870	А
I <sub>F,SM</sub>	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	115	А
I <sub>F,RM</sub>	Repetitive Forward Surge Current	Half–Sine Pulse, t <sub>p</sub> = 8.3 ms	50	А
P <sub>TOT</sub>	Power Dissipation	$T_{\rm C} = 25^{\circ}{\rm C}$	283	W
		T <sub>C</sub> = 150°C	47	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	•	-55 to +175	°C

#### ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = $25^{\circ}$ C unless otherwise noted)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

1. E <sub>AS</sub> of 145 m	sumed, damage may occur and J is based on starting T <sub>J</sub> = 25° HARACTERISTICS		= 50 V.	NDESI	_		
Symbol		Parameter		Value	Unit		
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction	n to Case, Max	10 CO	0.53	°C/W		
ELECTRICAL CHARACTERISTICS (T <sub>C</sub> = 25°C unless otherwise noted)							
Symbol	Parameter	Test Condition	Min Typ	Max	Unit		

ELECTRICAL CHARACTERISTICS (T <sub>C</sub> = 25°C unless otherwise noted)
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Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 15 A, T <sub>C</sub> = 25°C	10 <u>-</u> 14	1.45	1.75	V
		I <sub>F</sub> = 15 A, T <sub>C</sub> = 125°C	<u>R-111</u>	1.7	2.0	
		I <sub>F</sub> = 15 A, T <sub>C</sub> = 175°C	0	2.0	2.4	
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 1200 V, T <sub>C</sub> = 25°C	-	-	200	μΑ
	SEISN.	V <sub>R</sub> = 1200 V, T <sub>C</sub> = 125°C	-	-	300	
		V <sub>R</sub> = 1200 V, T <sub>C</sub> = 175°C	-	-	400	
Q <sub>C</sub>	Total Capacitive Charge	V = 800 V	-	95	-	nC
С	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	-	936	-	pF
	SV SEY.	V <sub>R</sub> = 400 V, f = 100 kHz	-	86	-	]
1Y		V <sub>R</sub> = 800 V, f = 100 kHz	_	68	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

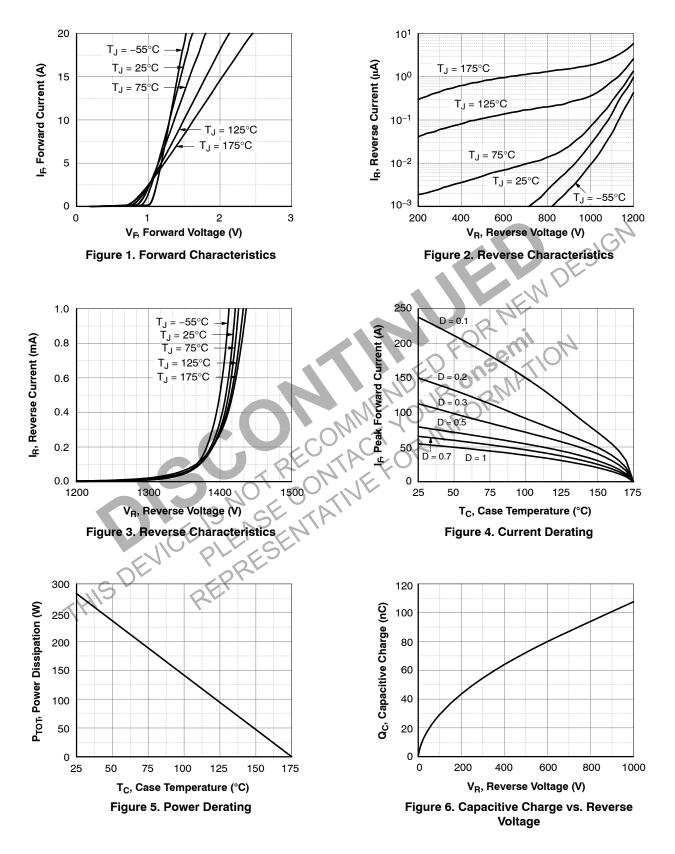
#### **ORDERING INFORMATION**

Part Number	Top Marking	Package	Packing Method	Quantity
FFSH15120A	FFSH15120A	TO-247-2LD	Tube	30 Units

### FFSH15120A

#### **TYPICAL CHARACTERISTICS**

(T<sub>J</sub> = 25°C UNLESS OTHERWISE NOTED)



#### **FFSH15120A**

 $\label{eq:typical characteristics} \begin{array}{l} \textbf{Typical characteristics} (\texttt{CONTINUED}) \\ (T_J = 25^\circ\texttt{C} \text{ UNLESS OTHERWISE NOTED}) \end{array}$ 

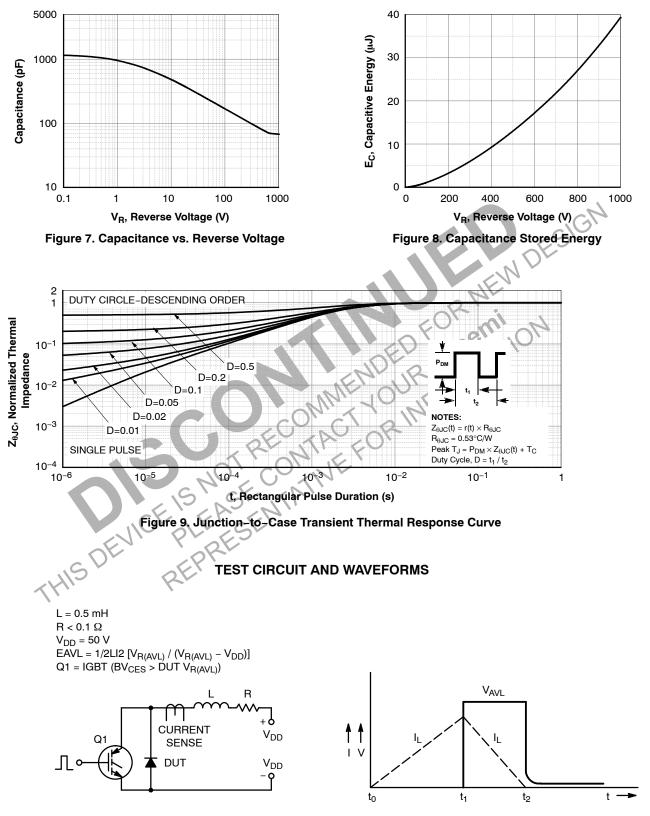


Figure 10. Unclamped Inductive Switching Test Circuit & Waveform

1

**MILLIMETERS** 

NOM

4.70

2.40

1.50

1.26

1.65

0.61

20.57

16.57

0.93

15.62

~

5.08

11.12

16.00

3.81

3.58

6.73

5.46

5.46

MAX

4.82

2.66

1.70

1.35

1.77

0.71

20.82

16.77

1.35

15.87

~

5.20

~

16.25

3.93

3.65

6.85

5.58

5.58

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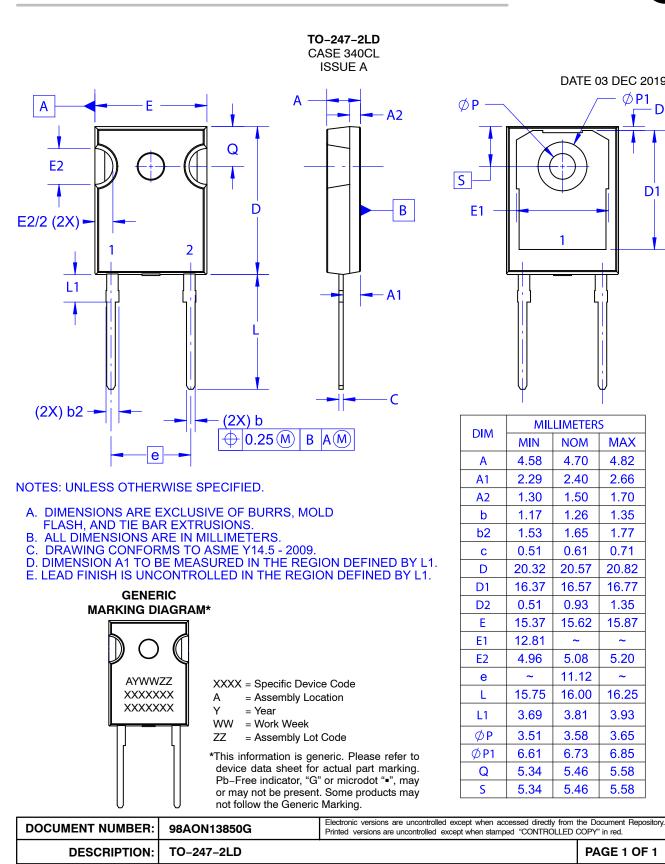
DATE 03 DEC 2019

ØP1



D2

D1



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